

BUK75/76/7E2R7-30B

TrenchMOS™ standard level FET

Rev. 03 — 13 October 2003

Product data

1. Product profile

1.1 Description

N-channel enhancement mode field-effect power transistor in a plastic package using Philips High-Performance Automotive (HPA) TrenchMOS™ technology.

1.2 Features

- Very low on-state resistance.
- 175 °C rated
- Q101 compliant
- Standard level compatible.

1.3 Applications

- Automotive systems
- Motors, lamps and solenoids
- 12 V loads
- General purpose power switching.

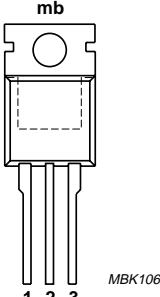
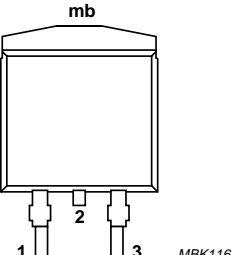
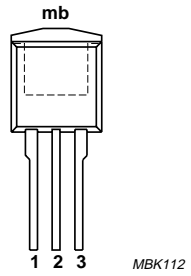
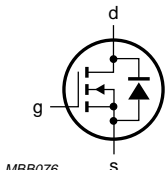
1.4 Quick reference data

- $E_{DS(AL)S} \leq 2.3 \text{ J}$
- $I_D \leq 75 \text{ A}$
- $R_{DS(on)} = 2.3 \text{ m}\Omega$ (typ)
- $P_{tot} \leq 300 \text{ W}$.

2. Pinning information

Table 1: Pinning - SOT78, SOT404, and SOT226 simplified outlines and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)		
2	drain (d) [1]		
3	source (s)		
mb	mounting base, connected to drain (d)		

			
SOT78 (TO-220AB)	SOT404 (D ² -PAK)	SOT226 (I ² -PAK)	MBB076

[1] It is not possible to make connection to pin 2 of the SOT404 package.

3. Ordering information

Table 2: Ordering information

Type number	Package		Version
	Name	Description	
BUK752R7-30B	TO-220AB	Plastic single-ended heat-sink mounted package	SOT78
BUK762R7-30B	D ² -PAK	Plastic single-ended surface mounted package	SOT404
BUK7E2R7-30B	I ² -PAK	Plastic single-ended low-profile package	SOT226

4. Limiting values

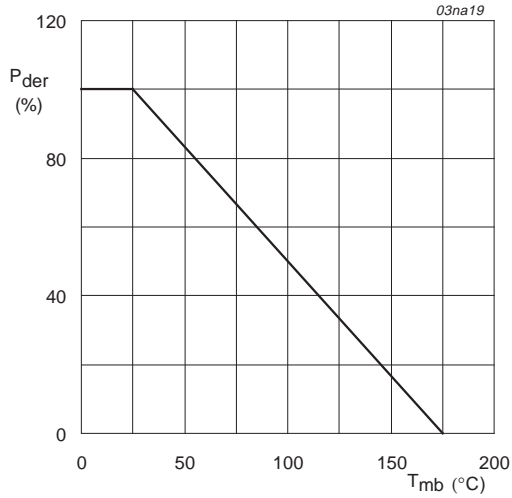
Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	30	V
V_{DGR}	drain-gate voltage (DC)	$R_{GS} = 20 \text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage (DC)		-	± 20	V
I_D	drain current (DC)	$T_{mb} = 25 \text{ }^\circ\text{C}$; $V_{GS} = 10 \text{ V}$; Figure 2 and 3	[1] -	241	A
			[2] -	75	A
		$T_{mb} = 100 \text{ }^\circ\text{C}$; $V_{GS} = 10 \text{ V}$; Figure 2	[2] -	75	A
I_{DM}	peak drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$; Figure 3	-	967	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$; Figure 1	-	300	W
T_{stg}	storage temperature		-55	+175	$^\circ\text{C}$
T_j	junction temperature		-55	+175	$^\circ\text{C}$
Source-drain diode					
I_{DR}	reverse drain current (DC)	$T_{mb} = 25 \text{ }^\circ\text{C}$	[1] -	241	A
			[2] -	75	A
I_{DRM}	peak reverse drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$	-	967	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 75 \text{ A}$; $V_{DS} \leq 30 \text{ V}$; $V_{GS} = 10 \text{ V}$; $R_{GS} = 50 \text{ }\Omega$; starting $T_{mb} = 25 \text{ }^\circ\text{C}$	-	2.3	J

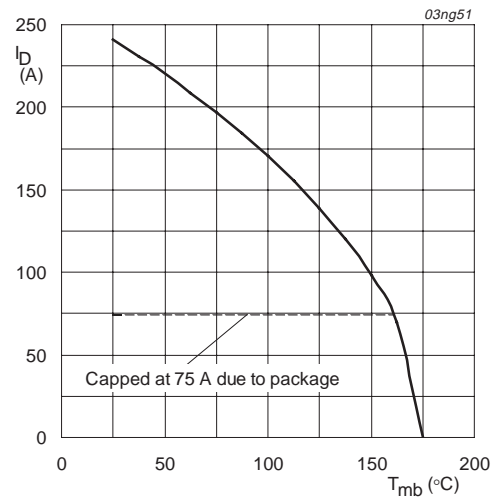
[1] Current is limited by power dissipation chip rating

[2] Continuous current is limited by package.



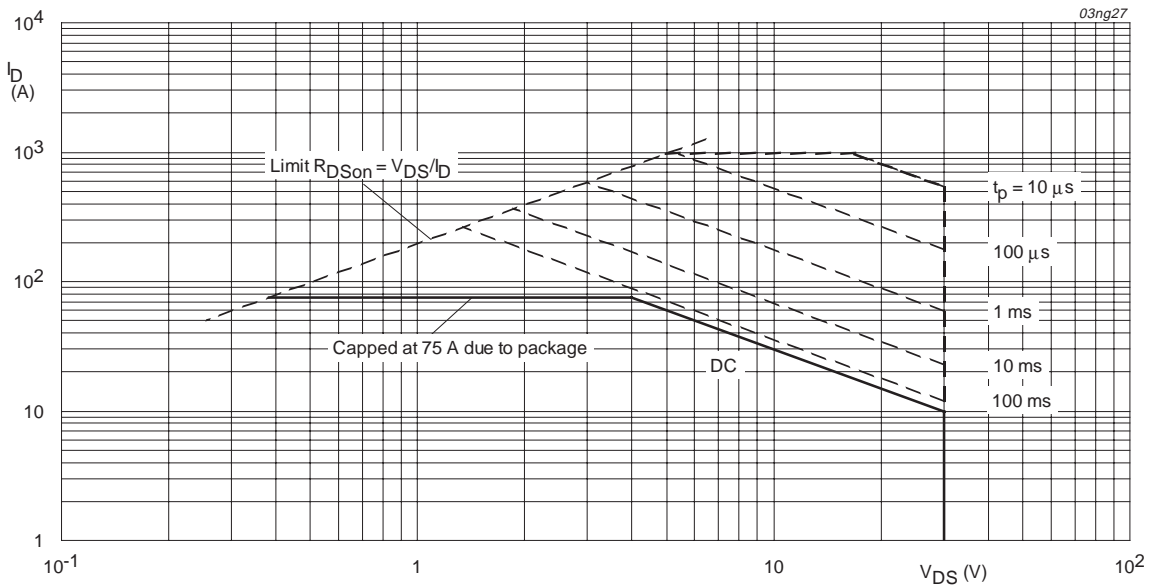
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$V_{GS} \geq 10\text{ V}$

Fig 2. Continuous drain current as a function of mounting base temperature.



$T_{mb} = 25^{\circ}C$; I_{DM} single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient					
	SOT78 (TO-220AB)	vertical in still air	-	60	-	K/W
	SOT226 (I ² -PAK)	vertical in still air	-	60	-	K/W
	SOT404 (D ² -PAK)	minimum footprint; mounted on a PCB	-	50	-	K/W

5.1 Transient thermal impedance

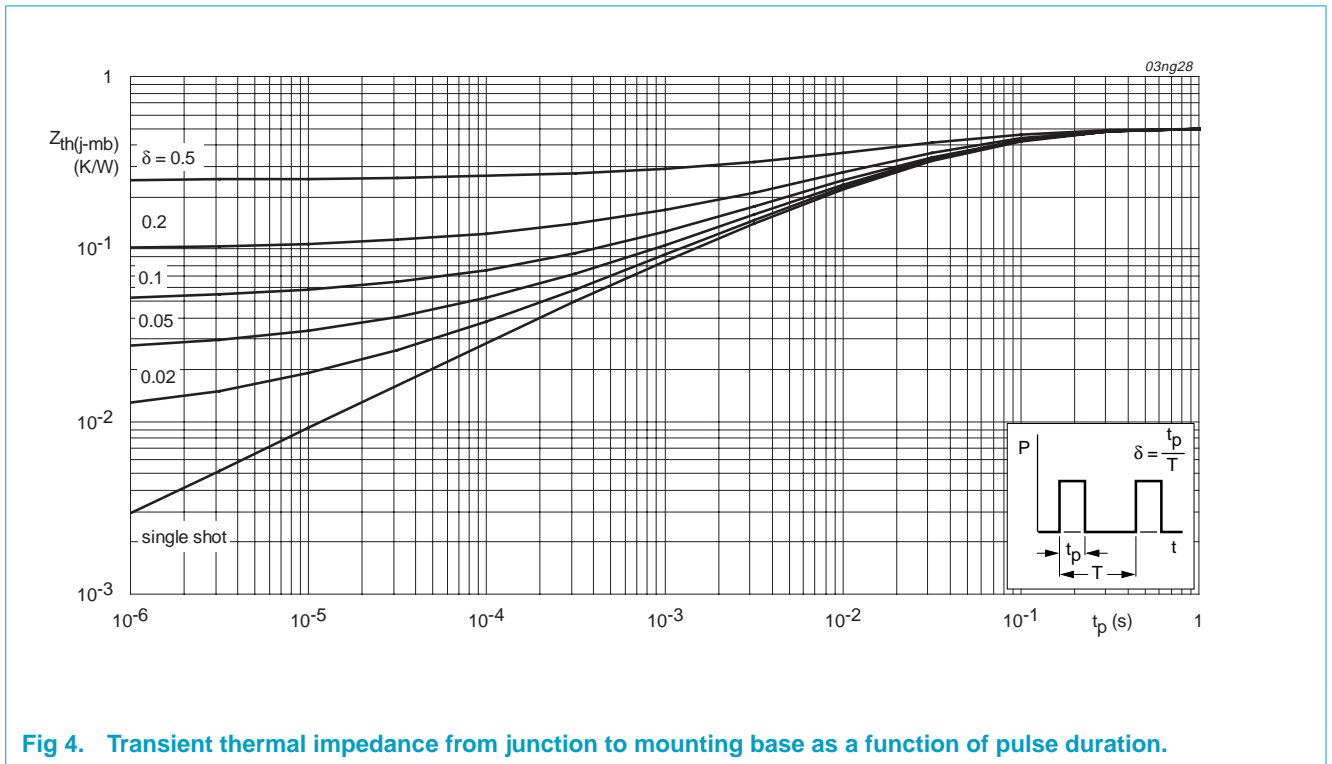


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

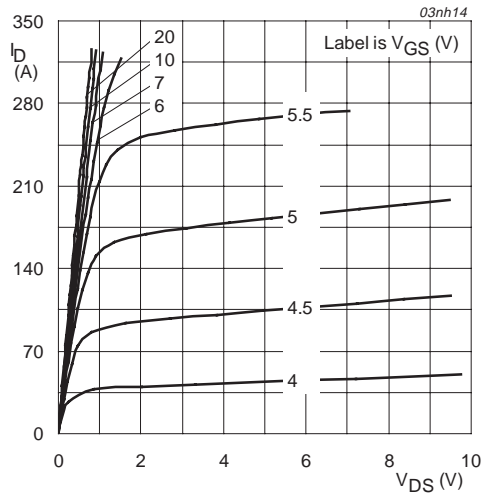
6. Characteristics

Table 5: Characteristics
T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V T _j = 25 °C	30	-	-	V
		T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; Figure 9				
		T _j = 25 °C	2	3	4	V
		T _j = 175 °C	1	-	-	V
		T _j = -55 °C	-	-	4.4	V
I _{DSS}	drain-source leakage current	V _{DS} = 30 V; V _{GS} = 0 V T _j = 25 °C	-	0.02	1	μA
		T _j = 175 °C	-	-	500	μA
I _{GSS}	gate-source leakage current	V _{GS} = ±20 V; V _{DS} = 0 V	-	2	100	nA
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; Figure 7 and 8				
		T _j = 25 °C	-	2.3	2.7	mΩ
		T _j = 175 °C	-	-	5.1	mΩ
Dynamic characteristics						
Q _{g(tot)}	total gate charge	V _{GS} = 10 V; V _{DD} = 24 V;	-	91	-	nC
Q _{gs}	gate-to-source charge	I _D = 25 A; Figure 14	-	19	-	nC
Q _{gd}	gate-to-drain (Miller) charge		-	29	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V;	-	4659	6212	pF
C _{oss}	output capacitance	f = 1 MHz; Figure 12	-	1691	2029	pF
C _{rss}	reverse transfer capacitance		-	622	852	pF
t _{d(on)}	turn-on delay time	V _{DD} = 30 V; R _L = 1.2 Ω;	-	31	-	ns
t _r	rise time	V _{GS} = 10 V; R _G = 10 Ω	-	107	-	ns
t _{d(off)}	turn-off delay time		-	113	-	ns
t _f	fall time		-	118	-	ns
L _d	internal drain inductance	from drain lead 6 mm from package to center of die	-	4.5	-	nH
		from contact screw on mounting base to center of die SOT78	-	3.5	-	nH
		from upper edge of drain mounting base to center of die SOT404/SOT226	-	2.5	-	nH
L _s	internal source inductance	from source lead to source bond pad	-	7.5	-	nH

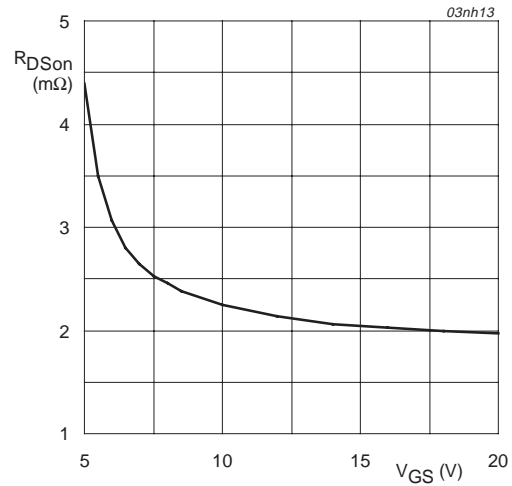
Table 5: Characteristics...continued*T_j = 25 °C unless otherwise specified*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V _{SD}	source-drain (diode forward) voltage	I _S = 40 A; V _{GS} = 0 V; Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs	-	88	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 20 V	-	132	-	nC



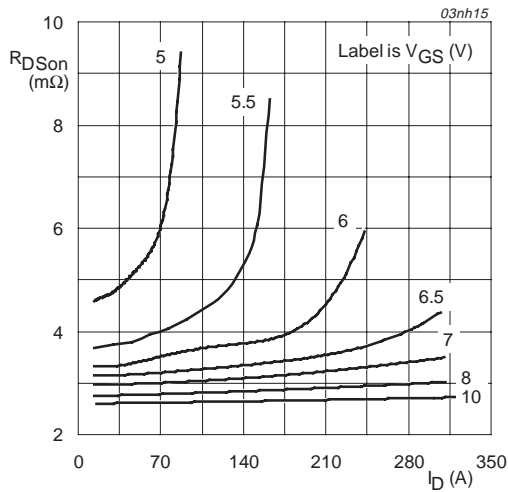
$T_j = 25\text{ }^\circ\text{C}$; $t_p = 300\text{ }\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



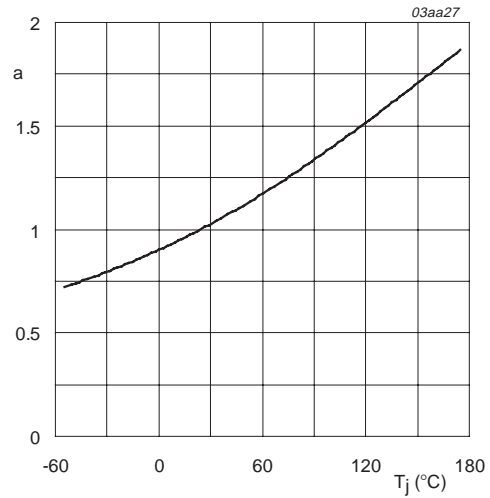
$T_j = 25\text{ }^\circ\text{C}$; $I_D = 25\text{ A}$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.



$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



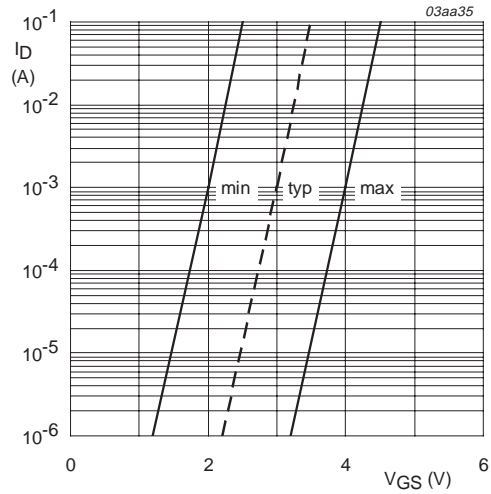
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



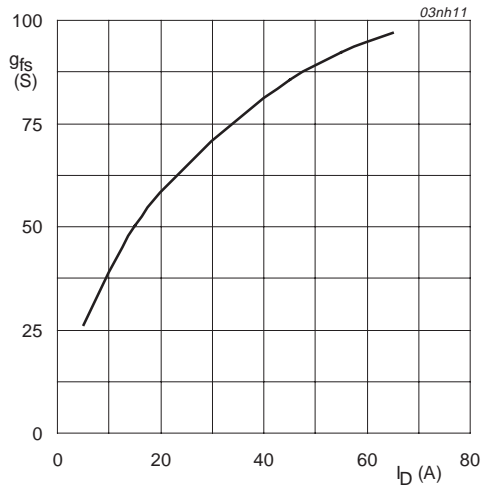
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



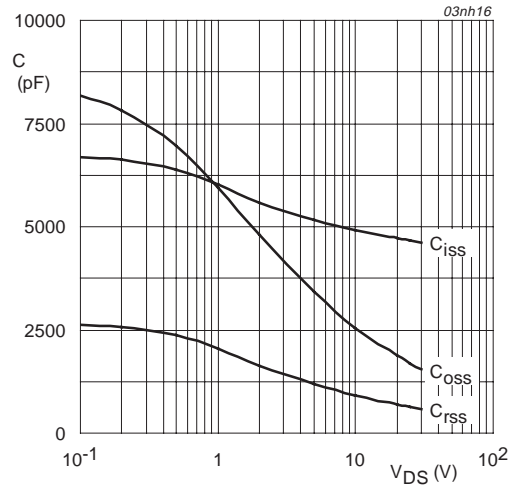
$T_j = 25 \text{ }^\circ\text{C}; V_{DS} = V_{GS}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



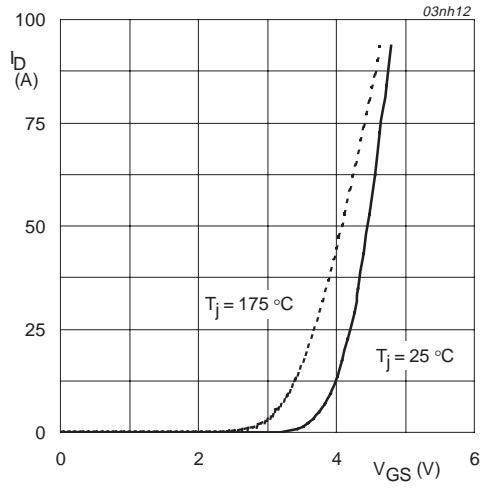
$T_j = 25 \text{ }^\circ\text{C}; V_{DS} = 25 \text{ V}$

Fig 11. Forward transconductance as a function of drain current; typical values.



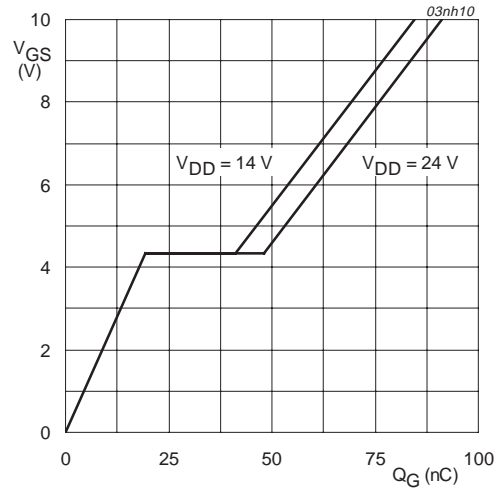
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



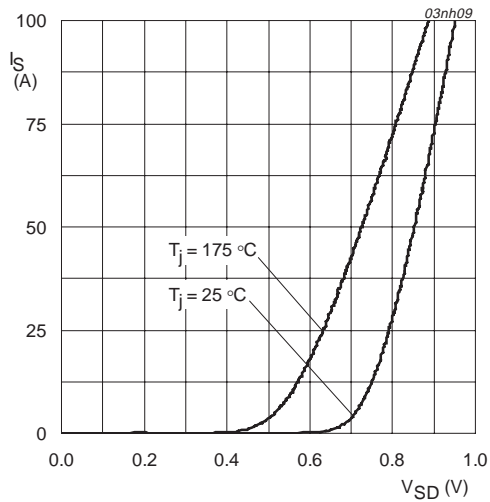
$V_{DS} = 25 \text{ V}$

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



$T_j = 25 \text{ °C}; I_D = 25 \text{ A}$

Fig 14. Gate-source voltage as a function of gate charge; typical values.



$V_{GS} = 0 \text{ V}$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



Fig 16. SOT78 (TO-220AB).

Plastic single-ended package; low-profile 3 lead TO-220AB

SOT226

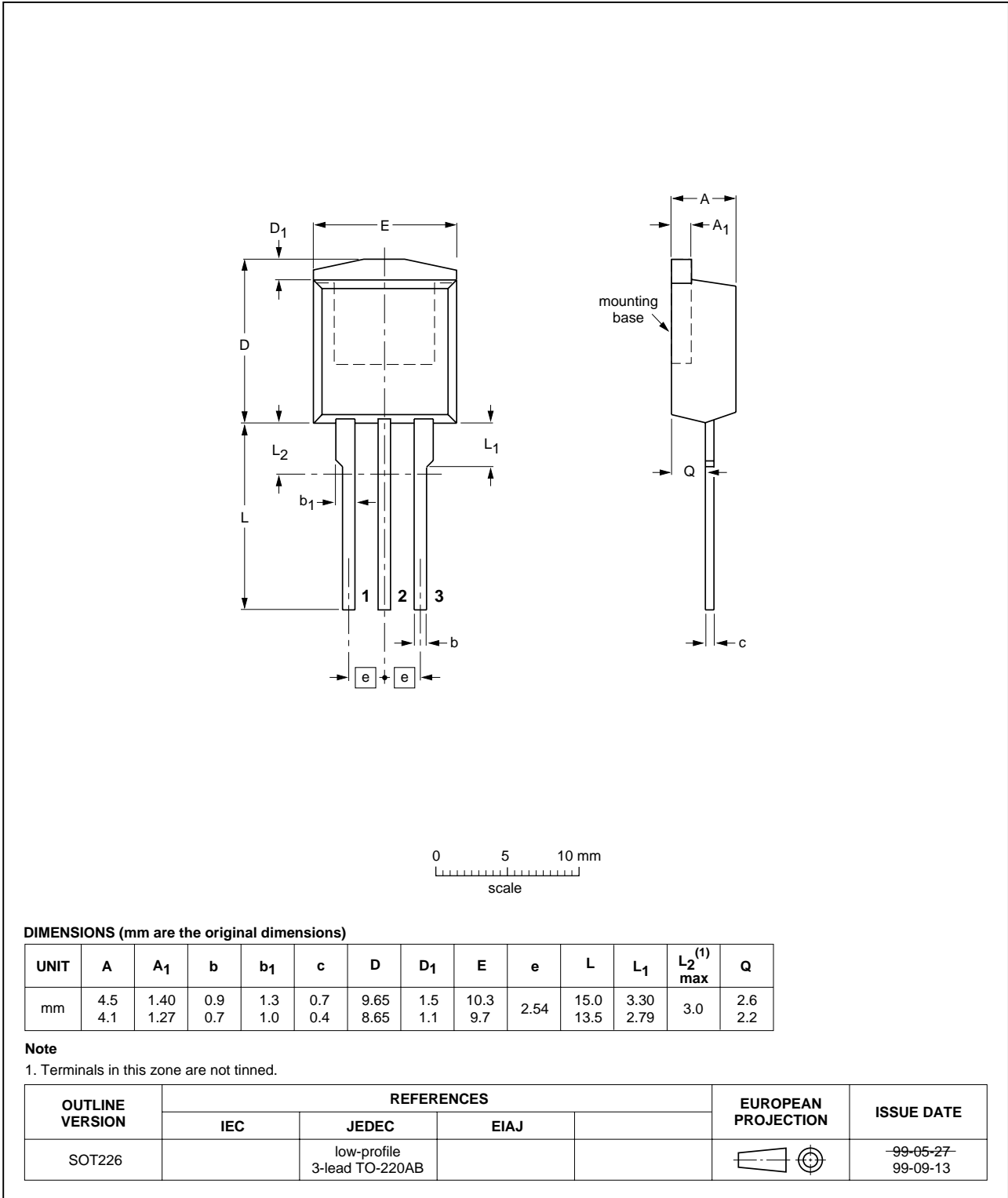


Fig 17. SOT226 (I²-PAK).

Plastic single-ended surface mounted package (Philips version of D²-PAK); 3 leads
(one lead cropped)

SOT404

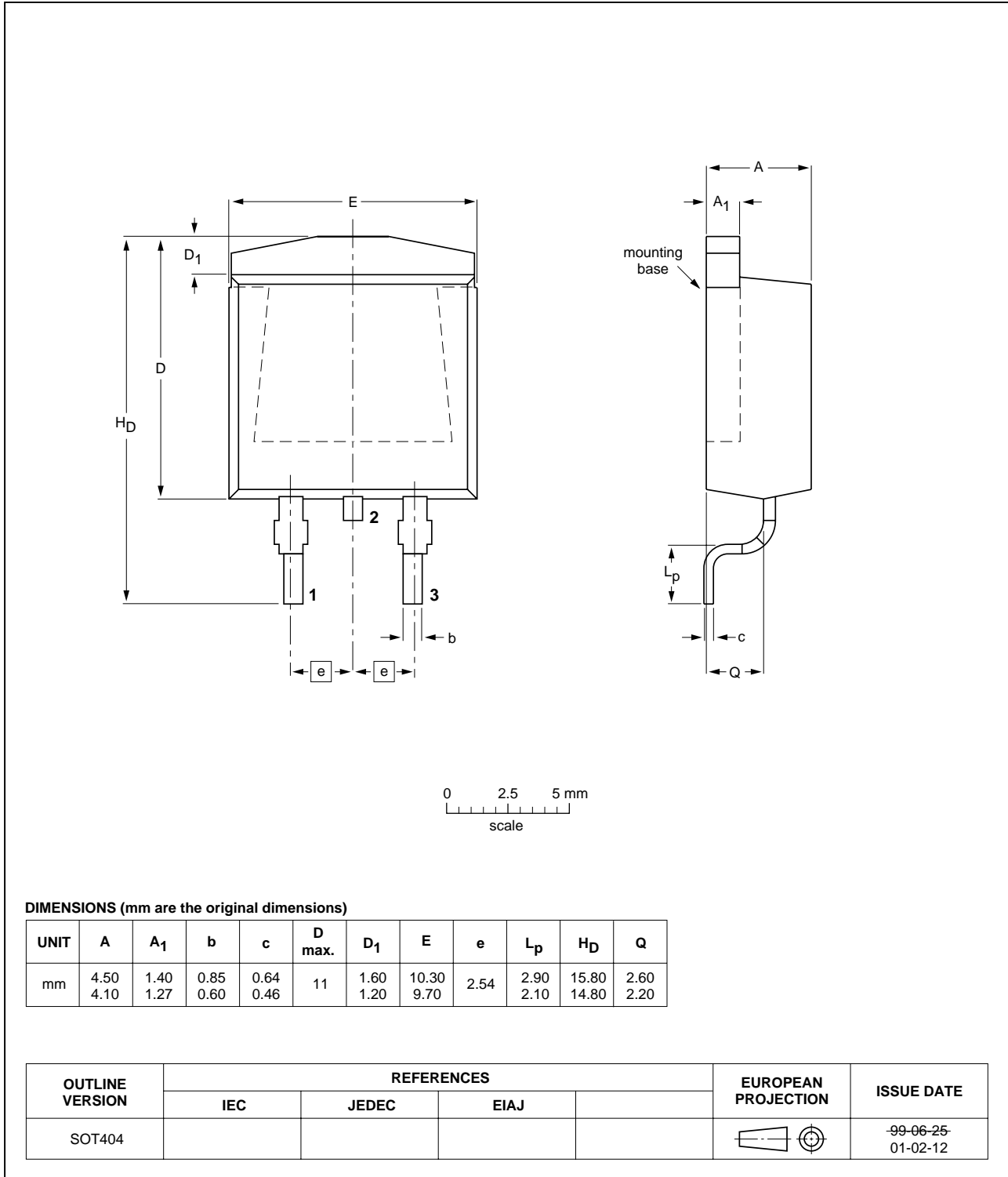
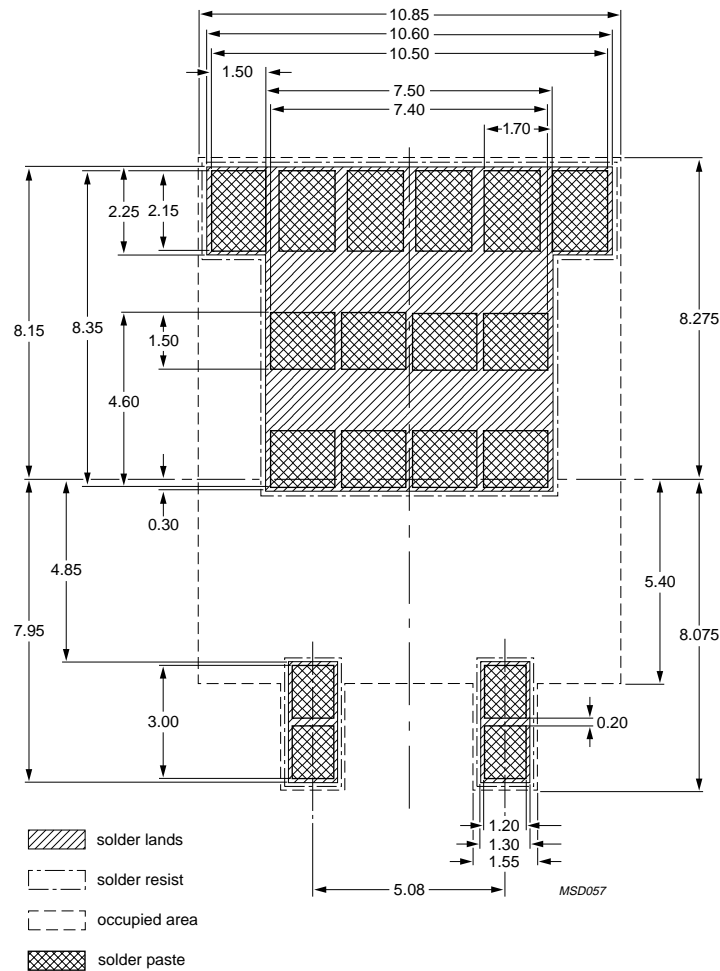


Fig 18. SOT404 (D²-PAK).

8. Soldering



Dimensions in mm.

Fig 19. Reflow soldering footprint for SOT404.

9. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
03	20031013	-	Product data (9397 750 12048) Modifications: <ul style="list-style-type: none">• Addition of BUK7E2R7-30B part to data sheet.
02	20021002	-	Product data (9397 750 10272) <ul style="list-style-type: none">• Description in Section 1 changed from: N-channel enhancement mode field-effect power transistor in a plastic package using generation three TrenchMOS™ technology, featuring very low on-state resistance. to: N-channel enhancement mode field-effect power transistor in a plastic package using Philips High-Performance Automotive TrenchMOS™ technology.
01	20020328	-	Product data (9397 750 09487)

10. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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